

# COMPUTER DIODE

General Purpose  
Switching

JAN & JANTX 1N3064  
1N4454; JAN, JANTX & JANTXV 1N4454  
JAN, JANTX & JANTXV 1N4454-1  
1N4532; JAN, JANTX & JANTXV 1N4532

## ABSOLUTE MAXIMUM RATINGS, AT 25°C

Reverse Breakdown Voltage	75V
Peak Working Voltage	50V
Average Output Current, 1N3064	75mA
1N4454,-1	200mA
1N4532	125mA
Surge Current, 1sec 1N3064	0.5A
1N4454,-1	1A
1N4532	0.5A
Operating Temperature Range	-65°C to +176°C
Storage Temperature Range	-65°C to +200°C

## FEATURES

- Metallurgical Bond
- Qualified to MIL-S-19500/144
- Planar Passivated Chip
- DO-7, DO-34 or DO-35 Package

## DESCRIPTION

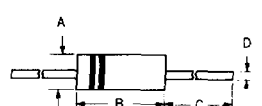
Available in DO-7, DO-34 or DO-35 packages. Microsemi offers high temperature metallurgical bond, making these devices useful in high reliability applications.

## ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

Type	Reverse Current @ 25°C	Reverse Current @ 150°C	Reverse Breakdown Voltage @ -65°C	Reverse Recovery Time	Capacitance	Forward Voltage	Forward Recovery Voltage	Forward Recovery Time
1N3064 1N4454 1N4454-1 1N4532	0.1µAdc @ V <sub>R</sub> = 50V	100µAdc @ V <sub>R</sub> = 50V	75Vdc @ I <sub>R</sub> = 5µAdc	4ns @ I <sub>F</sub> = I <sub>R</sub> = 10mAdc R <sub>L</sub> = 100Ω c ≤ 3pF	2pF @ V <sub>R</sub> = 0Vdc f = 1MHz V <sub>sig</sub> = 50mV (pk to pk)	1.0Vdc @ I <sub>F</sub> = 10mAdc	5.0V (pk) @ I <sub>F</sub> = 100mAdc t <sub>r</sub> ≤ 0.4ns	30ns I <sub>F</sub> = 100mAdc t <sub>r</sub> ≤ 0.4ns

## MECHANICAL SPECIFICATIONS


**J & JTX 1N3064**  
**J, JTX & JTXV 1N4454 & 1N4454-1**  
**J, JTX & JTXV 1N4532**



INCHES		MILLIMETERS	
A	.050-.065	1.27-1.65	
B	.080-.120	2.03-3.05	
C	1.0 MIN.-1.5 MAX.	24.0 MIN.-38.1 MAX.	
D	.018-.022	.46-.56	

INCHES		MILLIMETERS	
A	.078-.107	1.98-2.72	
B	.195-.300	4.96-7.62	
C	1.0 MIN.-1.5 MAX.	24.0 MIN.-38.1 MAX.	
D	.018-.022	.46-.56	

**DO-34**  
**1N4532**



**DO-35**  
**1N4454**

**Microsemi Corp.**  
**Watertown**  
*The diode experts*